





#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Features**

- Low On-Resistance
- Very Low Gate Threshold Voltage, 0.9V Max.
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- ESD Protected Gate
- Ultra Low Profile Package
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

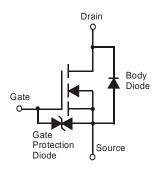
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper leadframe; Solderable per MIL-STD-202, Method 208@4
- Weight: 0.001 grams (Approximate)



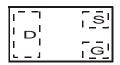


X2-DFN1006-3





**Equivalent Circuit** 



Top View Pin-Out

## **Ordering Information** (Note 4)

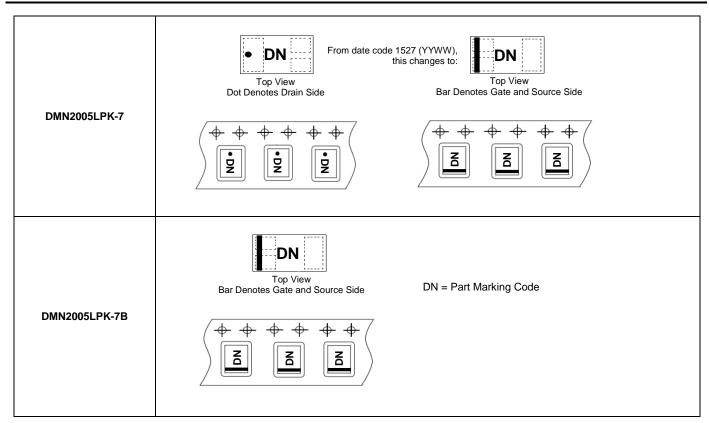
Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN2005LP4K-7	DN	7	8	3,000
DMN2005LP4K-7B	DN	7	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



# **Marking Information**





## Maximum Ratings (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	20	V
Gate-Source Voltage		V <sub>GSS</sub>	±10	V
Drain Current per element (Note 5)	Continuous Pulsed (Note 6)	I <sub>D</sub>	300 350	mA

## Thermal Characteristics (@TA = +25°C unless otherwise specified.)

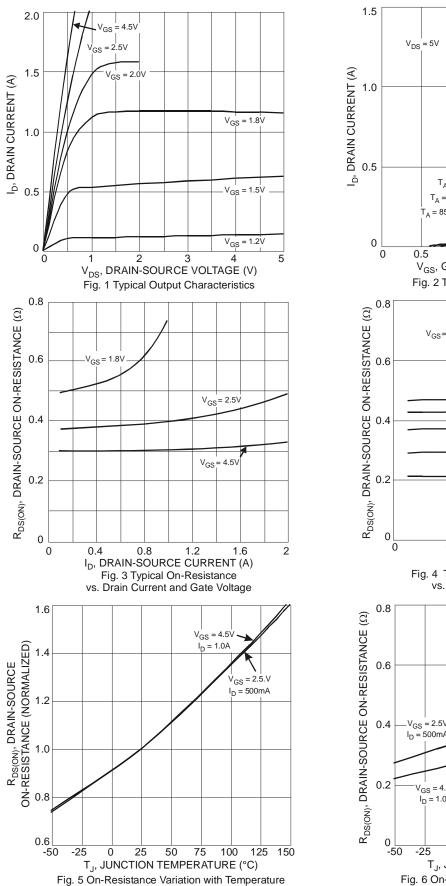
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	400	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	280	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

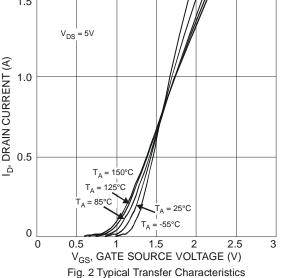
# Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (per element) (Note 7)							
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 100\mu A$
Zero Gate Voltage Drain Current		I <sub>DSS</sub>	_	_	10	μΑ	$V_{DS} = 17V$ , $V_{GS} = 0V$
Gate-Source Leakage		I <sub>GSS</sub>	_	_	±5	μΑ	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (per element) (Note 7)							
Gate Threshold Voltage		V <sub>GS(th)</sub>	0.53	_	0.9	V	$V_{DS} = V_{GS}$ , $I_D = 100\mu A$
Static Drain-Source On-Resistance		R <sub>DS</sub> (ON)		0.35 0.4 0.45 0.55 0.65	1.5 1.7 1.7 3.5 3.5	Ω	$V_{GS} = 4V, I_D = 10mA$ $V_{GS} = 2.7V, I_D = 200mA$ $V_{GS} = 2.5V, I_D = 10mA$ $V_{GS} = 1.8V, I_D = 200mA$ $V_{GS} = 1.5V, I_D = 1mA$
Forward Transfer Admittance		Y <sub>fs</sub>	40	_	_	mS	$V_{DS} = 3V, I_D = 10mA$
DYNAMIC CHARACTERISTICS							
Input Capacitance		C <sub>iss</sub>	_	37.1	_	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance		Coss	_	6.5	_	pF	
Reverse Transfer Capacitance		C <sub>rss</sub>	_	4.8	_	pF	1 = 1.000112
Switching Time	Turn-On Time Turn-Off Time	t <sub>on</sub>		4.06 13.7		nS	$V_{DD} = 10V, R_I = 47\Omega, V_{GEN} = 4.5V,$ $R_{GEN} = 10\Omega.$

- 5. Device mounted on FR-4 PCB.
- 6. Pulse width ≤10µS, Duty Cycle ≤1%.
  7. Short duration pulse test used to minimize self-heating effect.







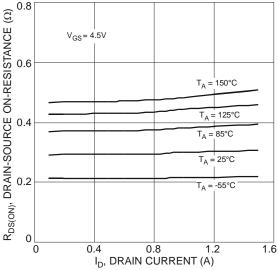


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

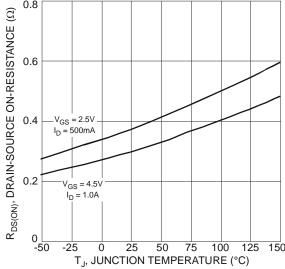


Fig. 6 On-Resistance Variation with Temperature



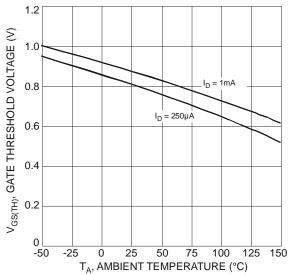
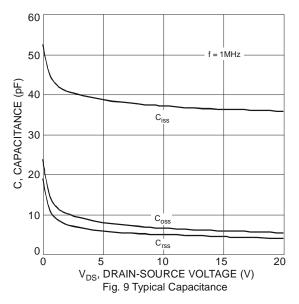
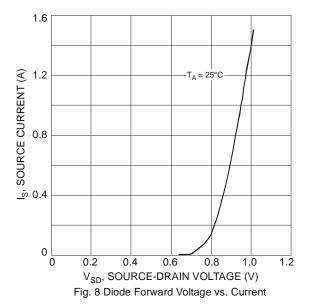


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

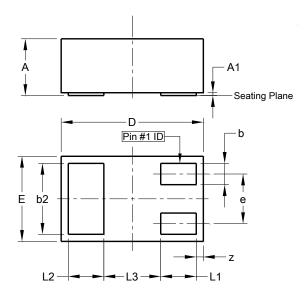






# **Package Outline Dimensions**

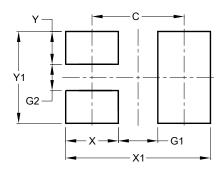
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN1006-3					
Dim	Min	Max	Тур		
Α		0.40	l		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.05	1.00		
Е	0.55	0.65	0.60		
е	1	1	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



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